PRODUCT FEATURES

☐ IGBT Chip(IGBT^3 Trench+Field Stop technology)，Diode Chip(Emcon3 wheeling diode)

☐ High level of integration—only one power semiconductor module required for the whole drive

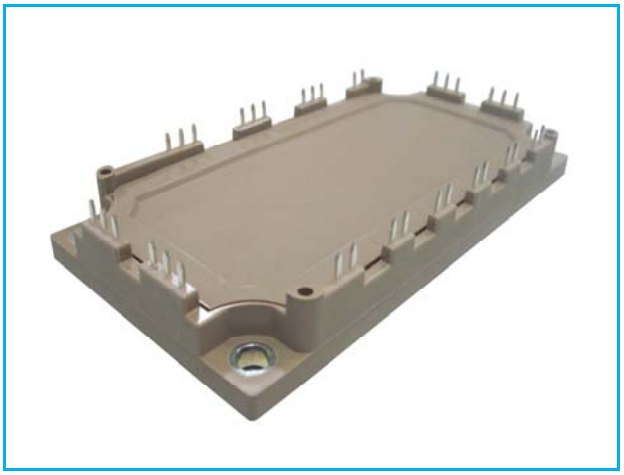
☐ Low saturation voltage and positive temperature coefficient

☐ Fast switching and short tail current

☐ Free wheeling diodes with fast and soft reverse recovery

☐ Industry standard package with insulated copper base plate and soldering pins for PCB mounting

☐ Temperature sense included



APPLICATIONS

☐ AC motor control

☐ Motion/servo control

☐ Inverter and power supplies

IGBT-inverter

ABSOLUTE MAXIMUM RATINGS(T_C *=25°C unless otherwise specified)*

Symbol	Parameter/Test Conditions		Values	Unit
V_{CES}	Collector Emitter Voltage	T_J=25℃	1200	V
V_{GES}	Gate Emitter Voltage		±20	
I_C	DC Collector Current	T_C=25℃, T_{Jmax}=150℃	140	A
		T_C=80℃, T_{Jmax}=150℃	100	
I_{CM}	Repetitive Peak Collector Current	tp=1ms	200	
P_{tot}	Power Dissipation Per IGBT	T_C=25℃, T_{Jmax}=150℃	450	W

Diode-inverter

ABSOLUTE MAXIMUM RATINGS (T_C *=25°C unless otherwise specified)*

Symbol	Parameter/Test Conditions		Values	Unit
V_{RRM}	Repetitive Reverse Voltage	T_J=25℃	1200	V
$I_{F(AV)}$	Average Forward Current		100	A
I_{FRM}	Repetitive Peak Forward Current	tp=1ms	200	
I^2t		T_J=125℃, t=10ms, V_R=0V	1850	A^2S

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IGBT-inverter

ELECTRICAL CHARACTERISTICS *(T_C=25°C unless otherwise specified)*

Symbol	Parameter/Test Conditions			Min.	Typ.	Max.	Unit
$V_{GE(th)}$	Gate Emitter Threshold Voltage	$V_{CE}=V_{GE}$, I_C=4mA		5.0	5.8	6.5	V
$V_{CE(sat)}$	Collector Emitter Saturation Voltage	I_C=100A, V_{GE}=15V, T_J=25℃			1.7	2.15	V
		I_C=100A, V_{GE}=15V, T_J=125℃			1.9		
I_{CES}	Collector Leakage Current	V_{CE}=1200V, V_{GE}=0V, T_J=25℃				100	μA
		V_{CE}=1200V, V_{GE}=0V, T_J=125℃				10	mA
I_{GES}	Gate Leakage Current	V_{CE}=0V,V_{GE}=±15V, T_J=25℃		-400		400	nA
R_{gint}	Integrated Gate Resistor				7.5		Ω
Q_g	Gate Charge	V_{CE}=600V, I_C=100A , V_{GE}=±15V			0.9		μC
C_{ies}	Input Capacitance	V_{CE}=25V, V_{GE}=0V, f =1MHz			7.1		nF
C_{res}	Reverse Transfer Capacitance				0.3		nF
$t_{d(on)}$	Turn on Delay Time	V_{CC}=600V,I_C=100A R_G =3.9Ω, V_{GE}=±15V, Inductive Load	T_J=25℃		260		ns
			T_J=125℃		290		ns
t_r	Rise Time		T_J=25℃		30		ns
			T_J=125℃		50		ns
$t_{d(off)}$	Turn off Delay Time	V_{CC}=600V,I_C=100A R_G =3.9Ω, V_{GE}=±15V, Inductive Load	T_J=25℃		420		ns
			T_J=125℃		520		ns
t_f	Fall Time		T_J=25℃		70		ns
			T_J=125℃		90		ns
E_{on}	Turn on Energy	V_{CC}=600V,I_C=100A R_G =3.9Ω, V_{GE}=±15V, Inductive Load	T_J=25℃		7.8		mJ
			T_J=125℃		10		mJ
E_{off}	Turn off Energy		T_J=25℃		8		mJ
			T_J=125℃		10		mJ
I_{SC}	Short Circuit Current	tpsc≤10μS , V_{GE}=15V T_J=125℃,V_{CC}=900V			400		A
R_{thJC}	Junction to Case Thermal Resistance （Per IGBT）					0.28	K /W

Diode-inverter

ELECTRICAL CHARACTERISTICS *(T_C=25°C unless otherwise specified)*

Symbol	Parameter/Test Conditions		Min.	Typ.	Max.	Unit
V_F	Forward Voltage	I_F=100A , V_{GE}=0V, T_J=25℃		1.65	2.15	V
		I_F=100A , V_{GE}=0V, T_J=125℃		1.65		
t_{rr}	Reverse Recovery Time	I_F=100A , V_R=600V dI_F/dt=-2500A/μs T_J=125℃		260		ns
I_{RRM}	Max. Reverse Recovery Current			140		A
Q_{RR}	Reverse Recovery Charge			20		μC
E_{rec}	Reverse Recovery Energy			9		mJ
R_{thJCD}	Junction to Case Thermal Resistance （Per Diode）				0.5	K /W

NTC CHARACTERISTICS *(T_C=25°C unless otherwise specified)*

Symbol	Parameter/Test Conditions		Min.	Typ.	Max.	Unit
R_{25}	Resistance	T_C =25℃		5		KΩ
$B_{25/50}$	$R_2 = R_{25} \exp [B_{25/50}(1/T_2 - 1/(298.15\ K))]$			3375		K

MODULE CHARACTERISTICS *(T_C=25°C unless otherwise specified)*

Symbol	Parameter/Test Conditions		Values	Unit
T_{Jmax}	Max. Junction Temperature		150	℃
T_{Jop}	Operating Temperature		-40~125	
T_{stg}	Storage Temperature		-40~125	
V_{isol}	Isolation Breakdown Voltage	AC, 50Hz(R.M.S), t=1minute	3000	V
CTI	Comparative Tracking Index		>200	
Md	Mounting Torque	Recommended（M5）	2.5~5	Nm
Weight			300	g

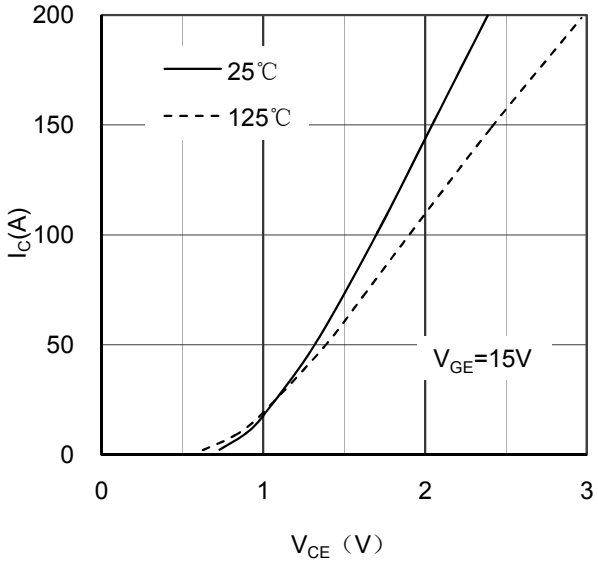


Figure 1. Typical Output Characteristics IGBT-inverter

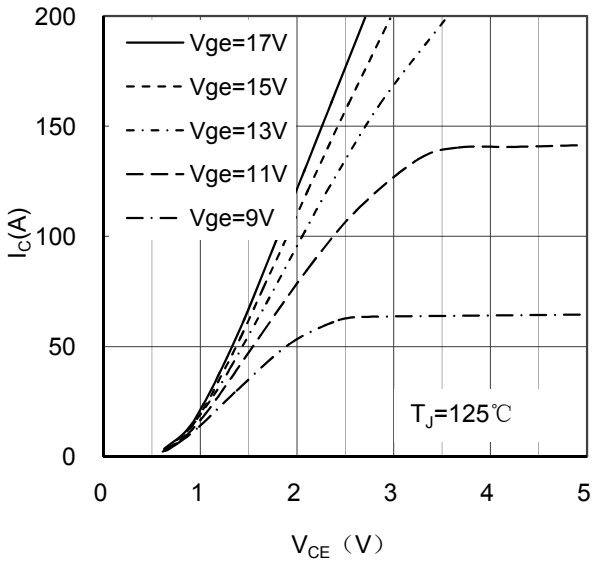


Figure 2. Typical Output Characteristics IGBT-inverter

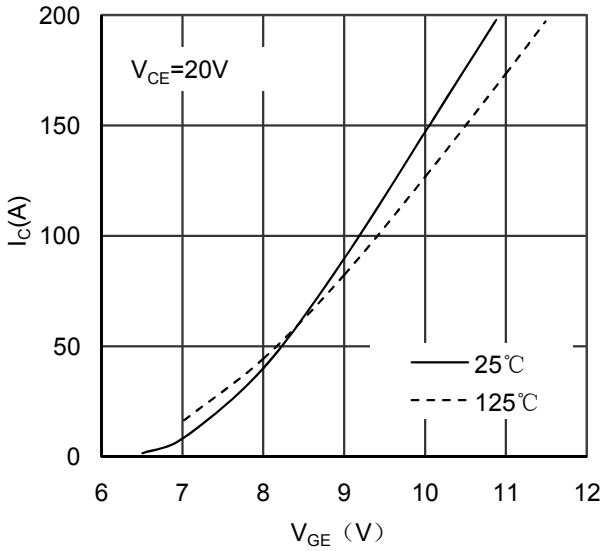


Figure 3. Typical Transfer characteristics IGBT-inverter

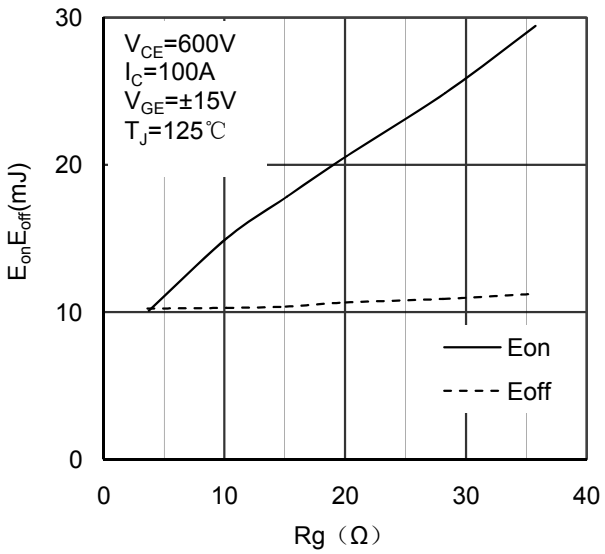


Figure 4. Switching Energy vs Gate Resistor IGBT-inverter

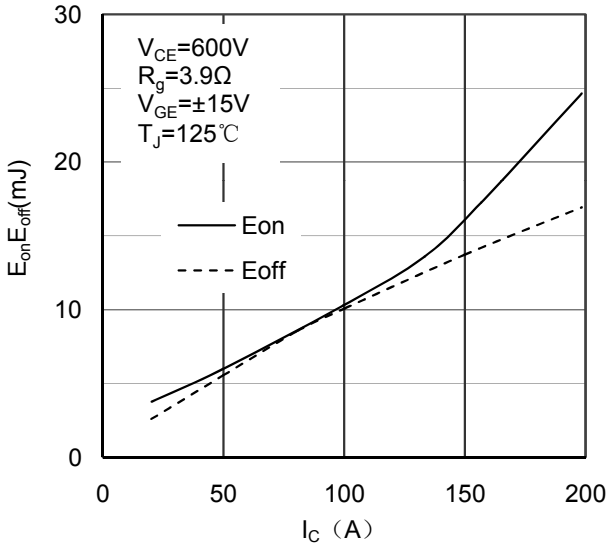


Figure 5. Switching Energy vs Collector Current IGBT-inverter

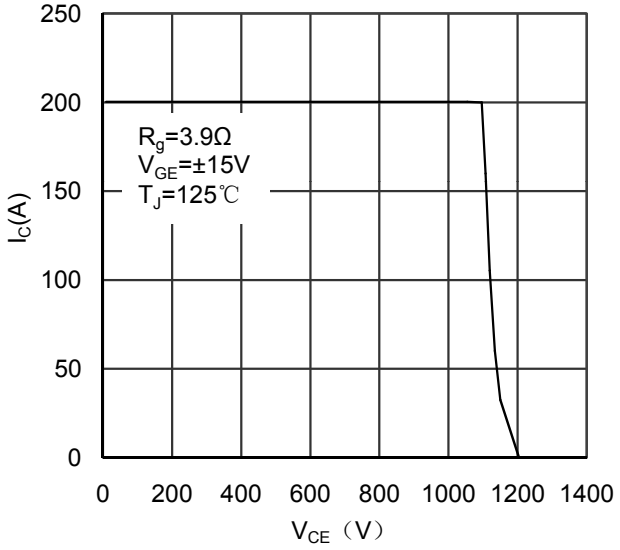


Figure 6. Reverse Biased Safe Operating Area IGBT-inverter

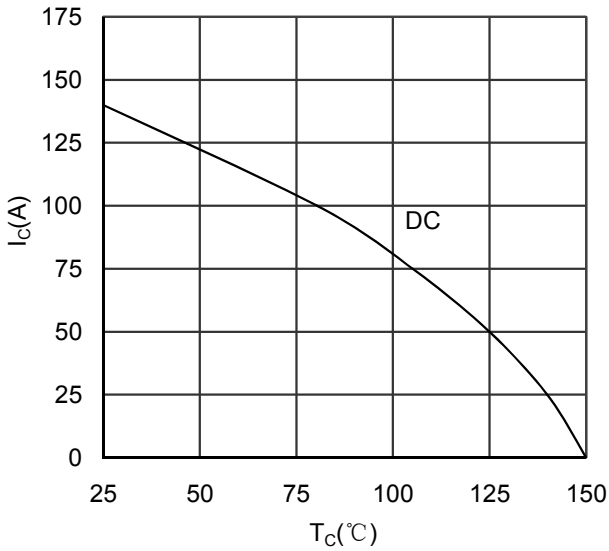


Figure 7. Collector Current vs Case temperature IGBT -inverter

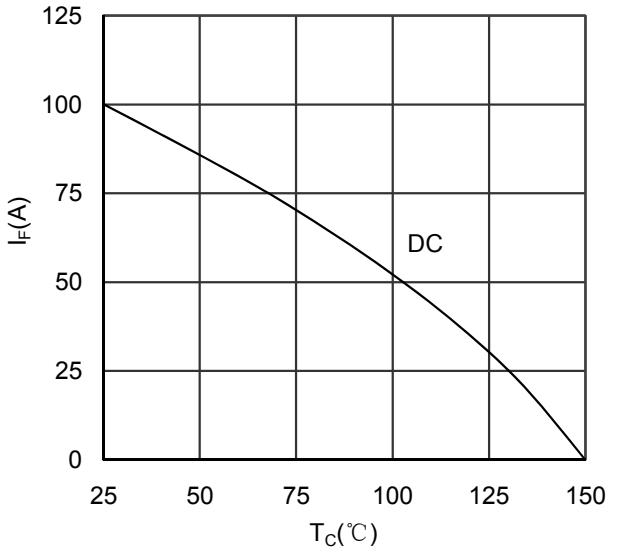


Figure 8. Forward current vs Case temperature Diode -inverter

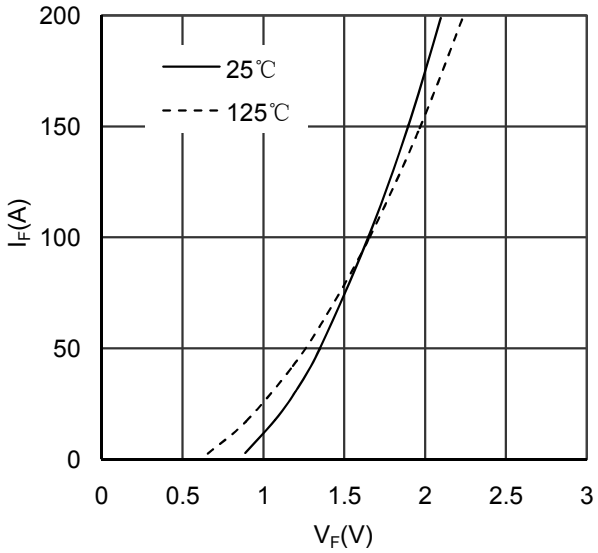


Figure 9. Diode Forward Characteristics Diode -inverter

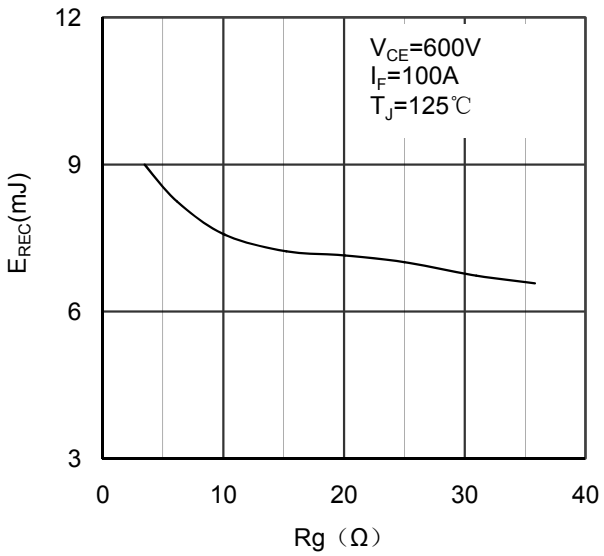


Figure 10. Switching Energy vs Gate Resistor Diode - inverter

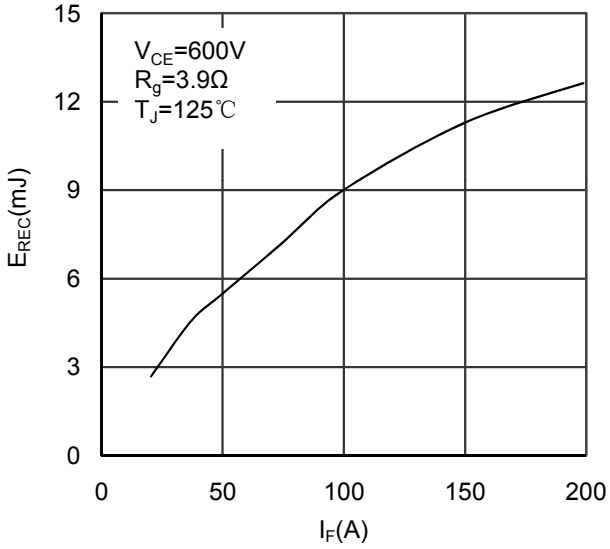


Figure 11. Switching Energy vs Forward Current Diode-inverter

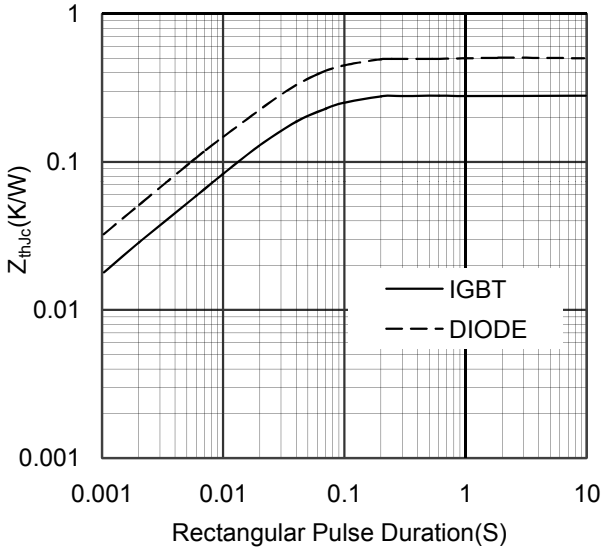


Figure 12. Transient Thermal Impedance of Diode and IGBT-inverter

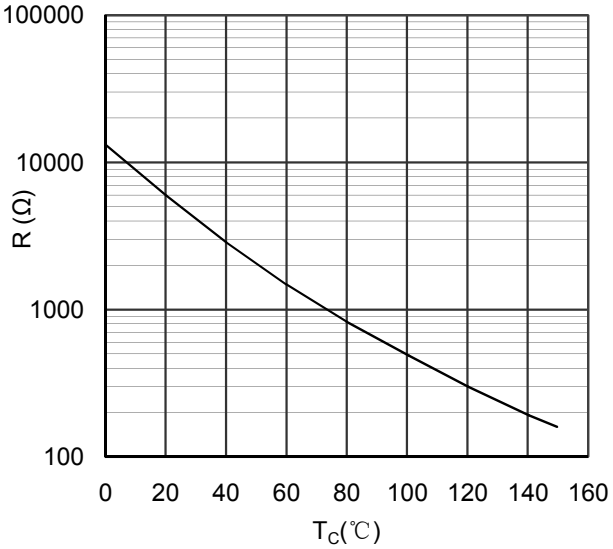


Figure 13. NTC Characteristics

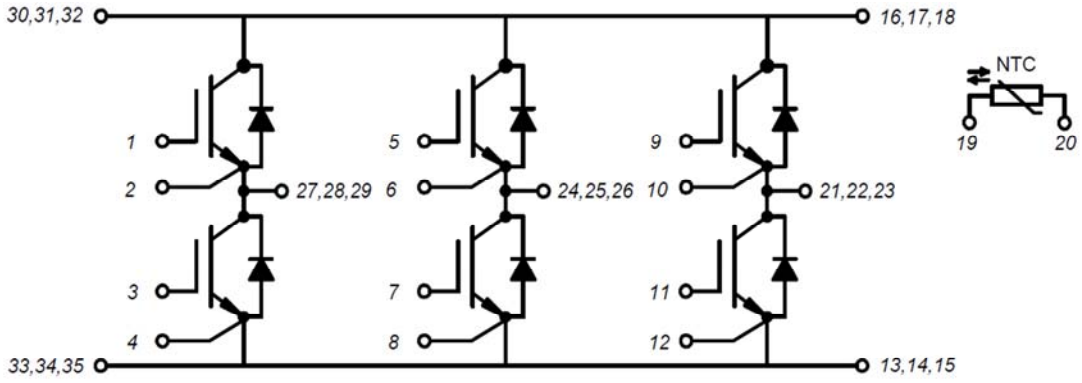
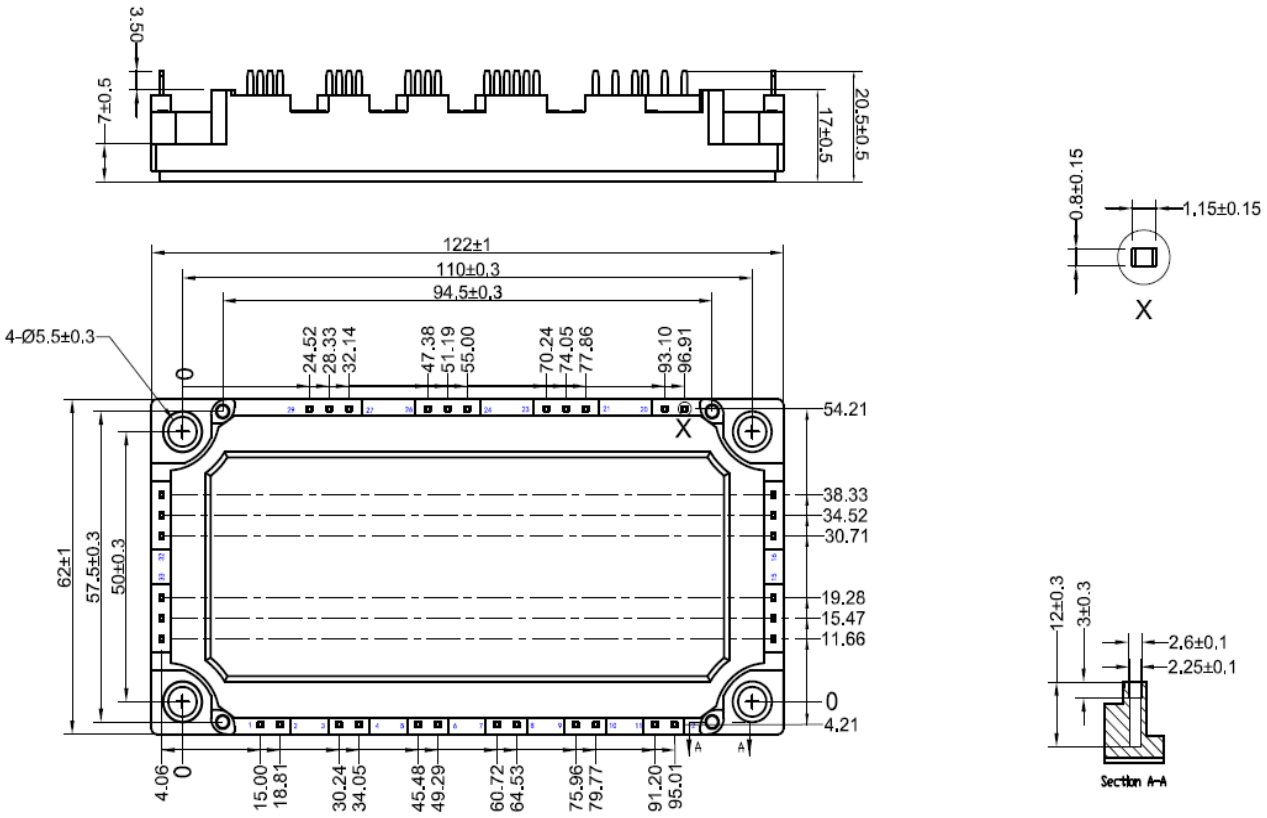


Figure 14. Circuit Diagram



Dimensions in (mm)

Figure 15. Package Outline